Plastic-Encapsulate Diodes

Schottky Barrier Diode

FEATURES

⌘Small Surface Mounting Type

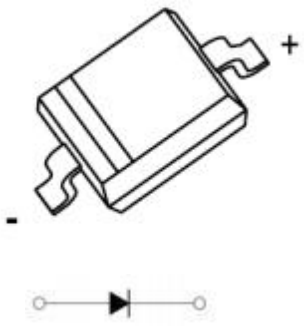
⌘Low V_F and I_R

⌘High Reliability

APPLICATIONS

⌘General Rectification

SOD-323



MARKING: SS

The marking bar indicates the cathode

MAXIMUM RATINGS (T_a =25℃ unless otherwise noted)

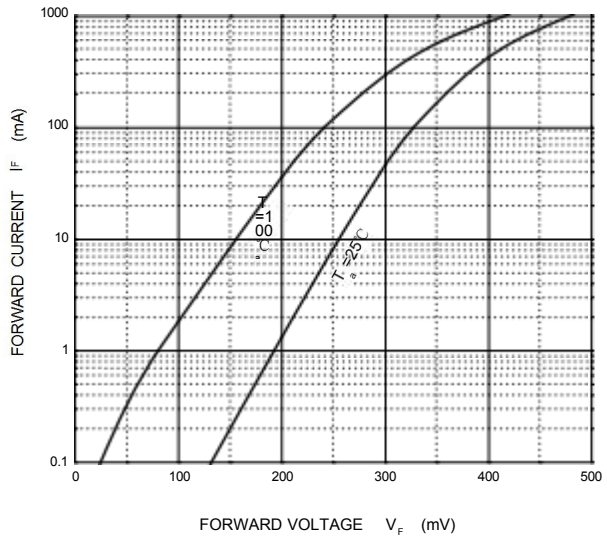
Symbol	Parameter	Value	Unit
V_{RM}	Non-Repetitive Peak Reverse Voltage	40	V
I_O	Continuous Forward Current	1	A
I_{FSM}	Non-repetitive Peak Forward Surge Current@t=8.3ms	3	A
P_D	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	500	℃/W
T_j	Junction Temperature	125	℃
T_{stg}	Storage Temperature	-55～+150	℃

ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise specified)

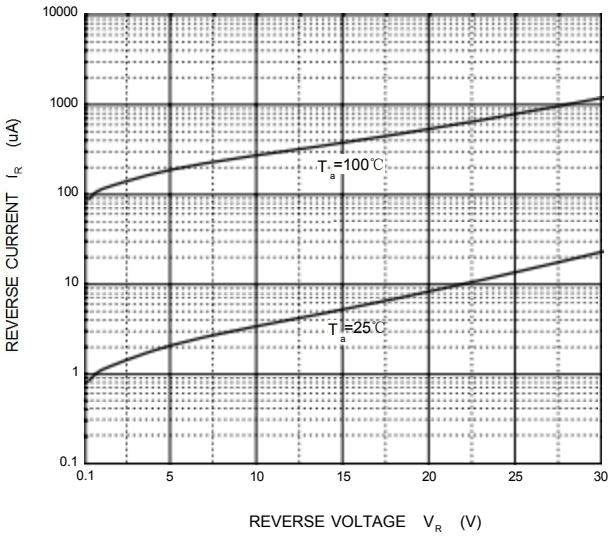
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	I_R=1mA	40			V
Reverse current	I_R	V_R=10V			0.03	mA
Forward voltage	V_F	I_F=700mA			0.49	V
		I_F=1A			0.56	

Typical Characteristics

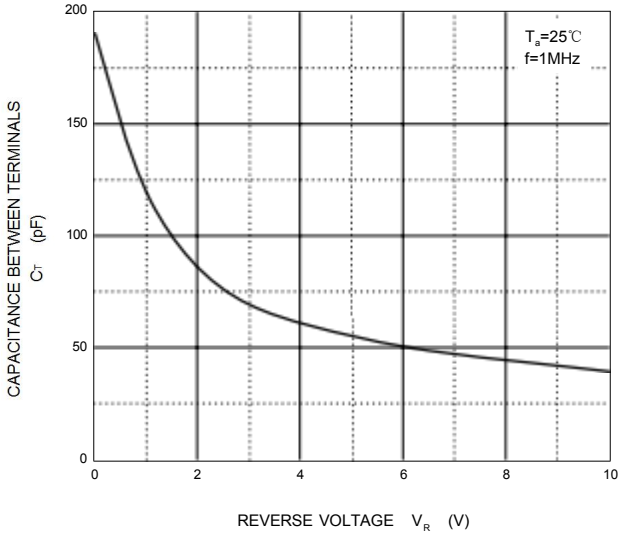
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve